



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	I _D max T _A = +25°C
	1.2Ω @ V _{GS} = 4V	415mA
30V	1.5Ω @ V _{GS} = 2.5V	370mA
	2.2Ω @ V _{GS} = 1.8V	300mA

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for highefficiency power management applications.

Applications

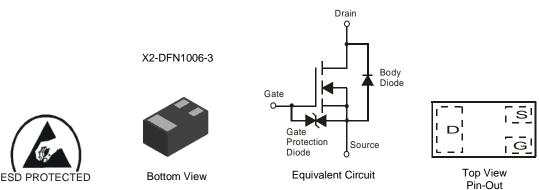
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.2V Max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@
- Weight: 0.001 grams (Approximate)



Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN32D2LFB4-7	DV	7	8	3,000
DMN32D2LFB4-7B	DV	7	8	10,000

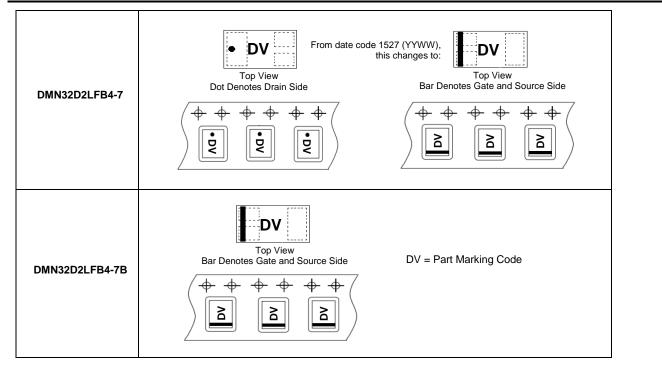
Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
 - <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



Maximum Ratings	$(@T_A = +25^{\circ}C, unless otherwise specified.)$
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Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±10	V
Drain Current (Note 5)	ID	300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Total Power Dissipation (Note 5) $@T_A = +25^{\circ}C$	PD	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

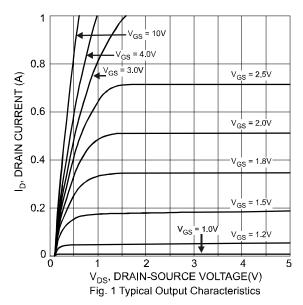
Note: 5. Device mounted on FR-4 PCB, pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

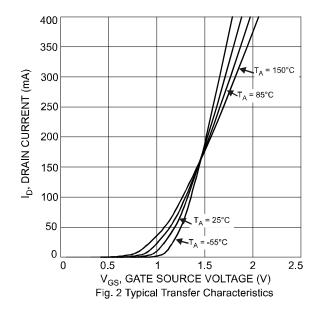


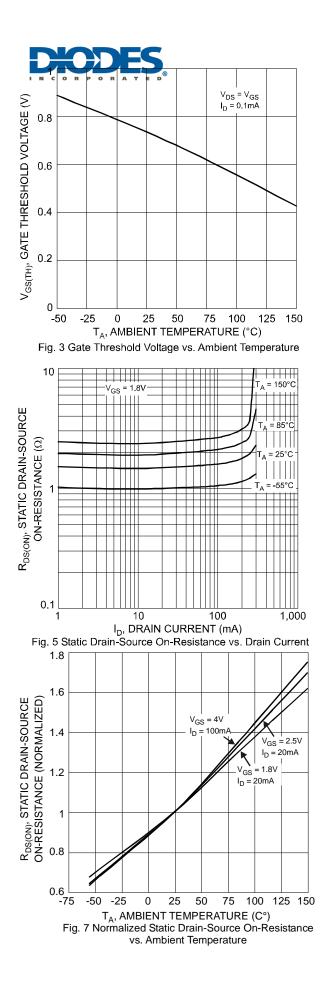
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

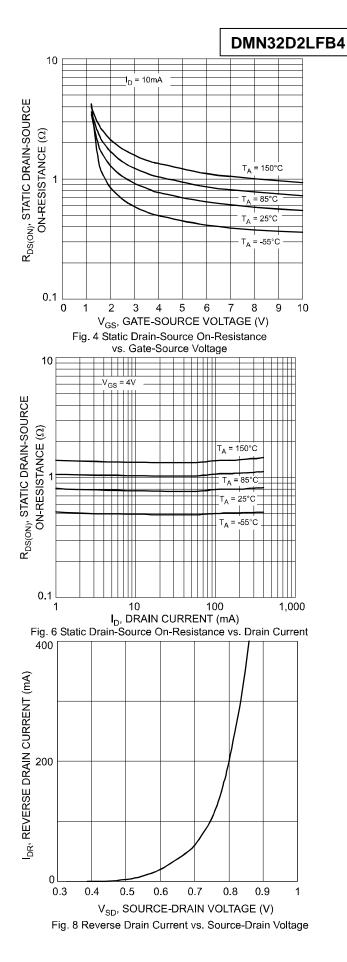
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					•	•	
Drain-Source Breakdown Voltage		BV _{DSS}	30	_	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ $T_{C} = +25^{\circ}C$	I _{DSS}	_	_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	±10 ±500	μA nA	$V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)					•		
Gate Threshold Voltage		V _{GS(th)}	0.6	—	1.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
			_	_	2.2		$V_{GS} = 1.8V, I_D = 20mA$
Static Drain-Source On-Resistance		R _{DS (ON)}	_		1.5	Ω	$V_{GS} = 2.5 V, I_D = 20 mA$
		, ,	—		1.2	i.	$V_{GS} = 4.0V, I_D = 100mA$
Forward Transconductance		Y _{fs}	100	_	_	mS	$V_{DS} = 10V, I_D = 0.1A$
Source-Drain Diode Forward Voltage		V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS							-
Input Capacitance		Ciss	_	39	78	pF	
Output Capacitance		Coss	_	10	20	pF	$V_{DS} = 3V, V_{GS} = 0V$
Reverse Transfer Capacitance		Crss		3.6	7.2	pF	f = 1.0MHz
Switching Time	Turn-on Time	t _{on}	_	11	22	nS	$V_{DD} = 5V, I_D = 10mA,$
Switching Time	Turn-off Time	toff	_	51	102	nS	$V_{GS} = 0.5V$

Note: 6. Short duration pulse test used to minimize self-heating effect.



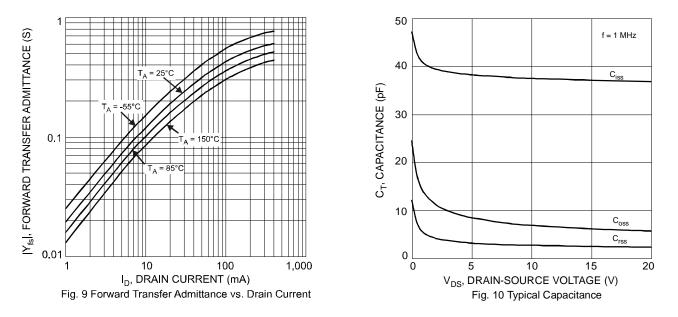






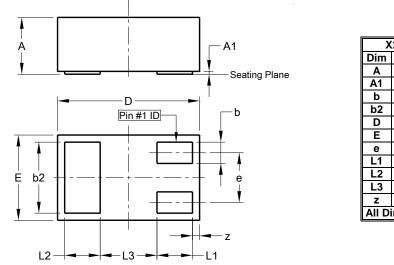


DMN32D2LFB4



Package Outline Dimensions

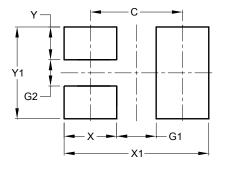
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3 Min Max Typ 0.40 0.00 0.05 0.03 0.10 0.20 0.15 0.45 0.55 0.50 0.95 1.05 1.00 0.55 0.65 0.60 0.35 --0.25 0.20 0.30 0.20 0.30 0.25 0.40 0.02 0.08 0.05 All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Ý	0.25
Y1	0.70



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